

# **2021 33rd International Symposium on Power Semiconductor Devices and ICs (ISPSD 2021)**

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## SESSION DETAILS

### MONDAY, MAY 31, 2021

12:10-12:40	<b>Opening session</b> Chairs: Kimimori Hamada ( <i>PDPlus LLC</i> ) Ichiro Omura ( <i>Kyushu Institute of Technology</i> )	Venue: <b>Nobunaga Room</b>
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## THURSDAY, JUNE 3, 2021

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